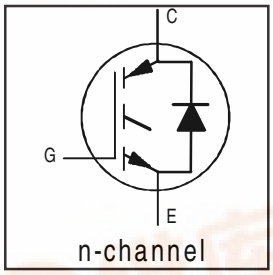
PD 91449B

International
IOR Rectifier

# IRG4BC20UD

## INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

UltraFast CoPack IGBT



n-channel

$V_{CES}$ = 600V

$V_{CE(on)\ typ.}$ = 1.85V

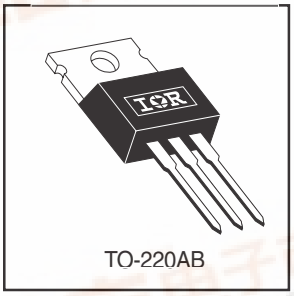
@$V_{GE}$ = 15V, $I_C$ = 6.5A

### Features

- UltraFast: optimized for high operating frequencies 8-40 kHz in hard switching, >200 kHz in resonant mode
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- IGBT co-packaged with HEXFRED® ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220AB package

### Benefits

- Generation -4 IGBTs offer highest efficiencies available
- IGBTs optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBTs. Minimized recovery characteristics require less/no snubbing
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBTs


TO-220AB

### Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---|---|---|---|
| $V_{CES}$ | Collector-to-Emitter Voltage | 600 | V |
| $I_C$ @ $T_C$ = 25°C | Continuous Collector Current | 13 | A |
| $I_C$ @ $T_C$ = 100°C | Continuous Collector Current | 6.5 | |
| $I_{CM}$ | Pulsed Collector Current ① | 52 | |
| $I_{LM}$ | Clamped Inductive Load Current ② | 52 | |
| $I_F$ @ $T_C$ = 100°C | Diode Continuous Forward Current | 7.0 | |
| $I_{FM}$ | Diode Maximum Forward Current | 52 | |
| $V_{GE}$ | Gate-to-Emitter Voltage | ± 20 | V |
| $P_D$ @ $T_C$ = 25°C | Maximum Power Dissipation | 60 | W |
| $P_D$ @ $T_C$ = 100°C | Maximum Power Dissipation | 24 | |
| $T_J$<br>$T_{STG}$ | Operating Junction and<br>Storage Temperature Range | -55 to +150 | °C |
| | Soldering Temperature, for 10 sec. | 300 (0.063 in. (1.6mm) from case) | |
| | Mounting Torque, 6-32 or M3 Screw. | 10 lbf•in (1.1 N•m) | |

### Thermal Resistance

| | Parameter | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction-to-Case - IGBT | ------ | ------ | 2.1 | °C/W |
| $R_{\theta JC}$ | Junction-to-Case - Diode | ------ | ------ | 3.5 | |
| $R_{\theta CS}$ | Case-to-Sink, flat, greased surface | ------ | 0.50 | ------ | |
| $R_{\theta JA}$ | Junction-to-Ambient, typical socket mount | ----- | ----- | 80 | |
| Wt | Weight | ------ | 2 (0.07) | ------ | g (oz) |



3/21/2000

## Electrical Characteristics @ $T_J$ = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---|---|---|---|---|---|---|
| $V_{(BR)CES}$ | Collector-to-Emitter Breakdown Voltage③ | 600 | ---- | ---- | V | $V_{GE}$ = 0V, $I_C$ = 250µA |
| $\Delta V_{(BR)CES}/\Delta T_J$ | Temperature Coeff. of Breakdown Voltage | ---- | 0.69 | ---- | V/°C | $V_{GE}$ = 0V, $I_C$ = 1.0mA |
| $V_{CE(on)}$ | Collector-to-Emitter Saturation Voltage | ---- | 1.85 | 2.1 | V | $I_C$ = 6.5A, $V_{GE}$ = 15V |
| | | ---- | 2.27 | ---- | | $I_C$ = 13A, See Fig. 2, 5 |
| | | ---- | 1.87 | ---- | | $I_C$ = 6.5A, $T_J$ = 150°C |
| $V_{GE(th)}$ | Gate Threshold Voltage | 3.0 | ---- | 6.0 | | $V_{CE}$ = $V_{GE}$, $I_C$ = 250µA |
| $\Delta V_{GE(th)}/\Delta T_J$ | Temperature Coeff. of Threshold Voltage | ---- | -11 | ---- | mV/°C | $V_{CE}$ = $V_{GE}$, $I_C$ = 250µA |
| $g_{fe}$ | Forward Transconductance ④ | 1.4 | 4.3 | ---- | S | $V_{CE}$ = 100V, $I_C$ = 6.5A |
| $I_{CES}$ | Zero Gate Voltage Collector Current | ---- | ---- | 250 | µA | $V_{GE}$ = 0V, $V_{CE}$ = 600V |
| | | ---- | ---- | 1700 | | $V_{GE}$ = 0V, $V_{CE}$ = 600V, $T_J$ = 150°C |
| $V_{FM}$ | Diode Forward Voltage Drop | ---- | 1.4 | 1.7 | V | $I_C$ = 8.0A, See Fig. 13 |
| | | ---- | 1.3 | 1.6 | | $I_C$ = 8.0A, $T_J$ = 150°C |
| $I_{GES}$ | Gate-to-Emitter Leakage Current | ---- | ---- | ±100 | nA | $V_{GE}$ = ±20V |

## Switching Characteristics @ $T_J$ = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---|---|---|---|---|---|---|
| $Q_g$ | Total Gate Charge (turn-on) | ---- | 27 | 41 | nC | $I_C$ = 6.5A |
| Qge | Gate - Emitter Charge (turn-on) | ---- | 4.5 | 6.8 | | $V_{CC}$ = 400V See Fig. 8 |
| $Q_{gc}$ | Gate - Collector Charge (turn-on) | ---- | 10 | 16 | | $V_{GE}$ = 15V |
| $t_{d(on)}$ | Turn-On Delay Time | ---- | 39 | ---- | ns | $T_J$ = 25°C |
| $t_r$ | Rise Time | ---- | 15 | ---- | | $I_C$ = 6.5A, $V_{CC}$ = 480V |
| $t_{d(off)}$ | Turn-Off Delay Time | ---- | 93 | 140 | | $V_{GE}$ = 15V, $R_G$ = 50Ω |
| $t_f$ | Fall Time | ---- | 110 | 170 | | Energy losses include "tail" and |
| $E_{on}$ | Turn-On Switching Loss | ---- | 0.16 | ---- | mJ | diode reverse recovery. |
| $E_{off}$ | Turn-Off Switching Loss | ---- | 0.13 | ---- | | See Fig. 9, 10, 11, 18 |
| $E_{ts}$ | Total Switching Loss | ---- | 0.29 | 0.3 | | |
| $t_{d(on)}$ | Turn-On Delay Time | ---- | 38 | ---- | ns | $T_J$ = 150°C, See Fig. 9, 10, 11, 18 |
| $t_r$ | Rise Time | ---- | 17 | ---- | | $I_C$ = 6.5A, $V_{CC}$ = 480V |
| $t_{d(off)}$ | Turn-Off Delay Time | ---- | 100 | ---- | | $V_{GE}$ = 15V, $R_G$ = 50Ω |
| $t_f$ | Fall Time | ---- | 220 | ---- | | Energy losses include "tail" and |
| $E_{ts}$ | Total Switching Loss | ---- | 0.49 | ---- | mJ | diode reverse recovery. |
| $L_E$ | Internal Emitter Inductance | ---- | 7.5 | ---- | nH | Measured 5mm from package |
| $C_{ies}$ | Input Capacitance | ---- | 530 | ---- | pF | $V_{GE}$ = 0V |
| $C_{oes}$ | Output Capacitance | ---- | 39 | ---- | | $V_{CC}$ = 30V See Fig. 7 |
| $C_{res}$ | Reverse Transfer Capacitance | ---- | 7.4 | ---- | | $f$ = 1.0MHz |
| $t_{rr}$ | Diode Reverse Recovery Time | ---- | 37 | 55 | ns | $T_J$ = 25°C See Fig. |
| | | ---- | 55 | 90 | | $T_J$ = 125°C 14 $I_F$ = 8.0A |
| $I_{rr}$ | Diode Peak Reverse Recovery Current | ---- | 3.5 | 5.0 | A | $T_J$ = 25°C See Fig. |
| | | ---- | 4.5 | 8.0 | | $T_J$ = 125°C 15 $V_R$ = 200V |
| $Q_{rr}$ | Diode Reverse Recovery Charge | ---- | 65 | 138 | nC | $T_J$ = 25°C See Fig. |
| | | ---- | 124 | 360 | | $T_J$ = 125°C 16 di/dt 200A/µs |
| $di_{(rec)M}/dt$ | Diode Peak Rate of Fall of Recovery | ---- | 240 | ---- | A/µs | $T_J$ = 25°C See Fig. |
| | During $t_b$ | ---- | 210 | ---- | | $T_J$ = 125°C 17 |

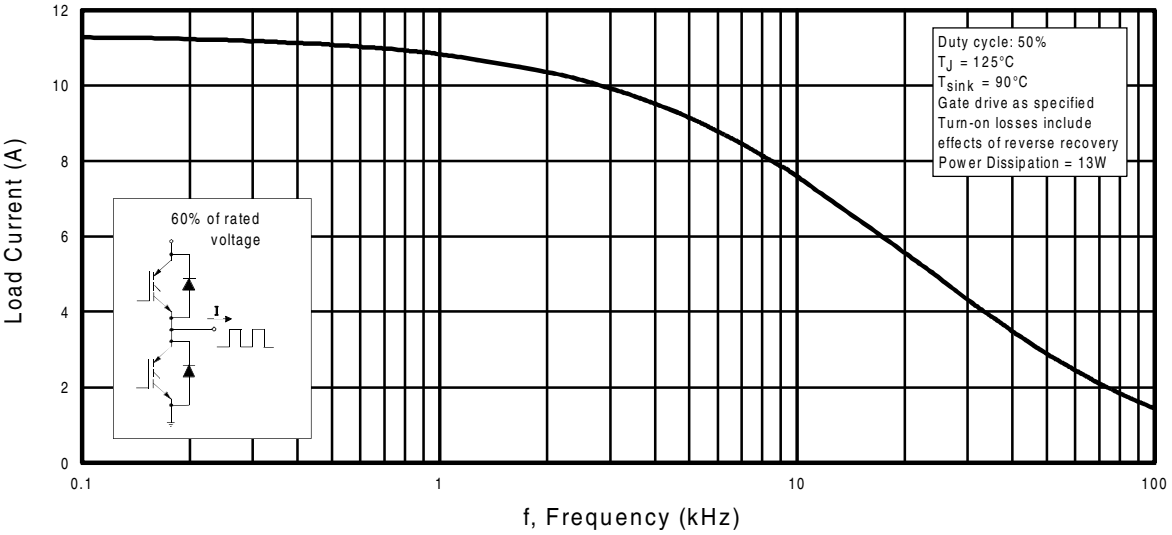



**Fig. 1** - Typical Load Current vs. Frequency
(Load Current = $I_{RMS}$ of fundamental)

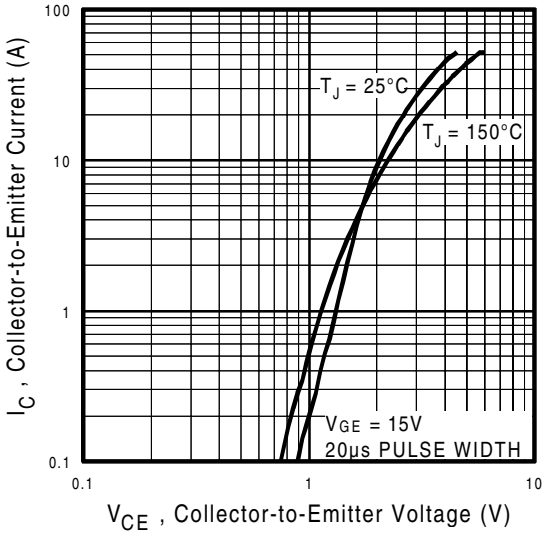



**Fig. 2** - Typical Output Characteristics

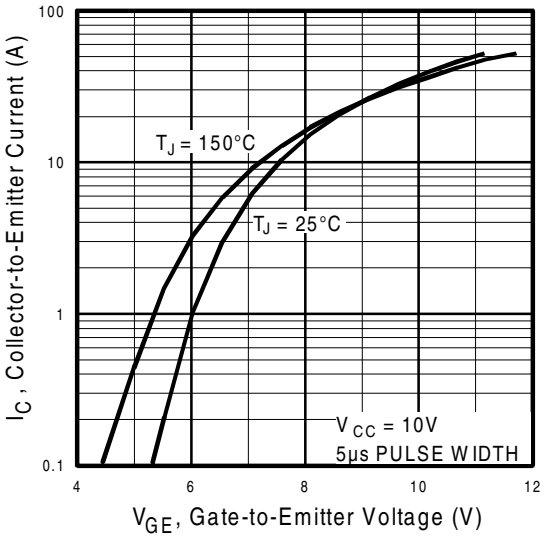



**Fig. 3** - Typical Transfer Characteristics

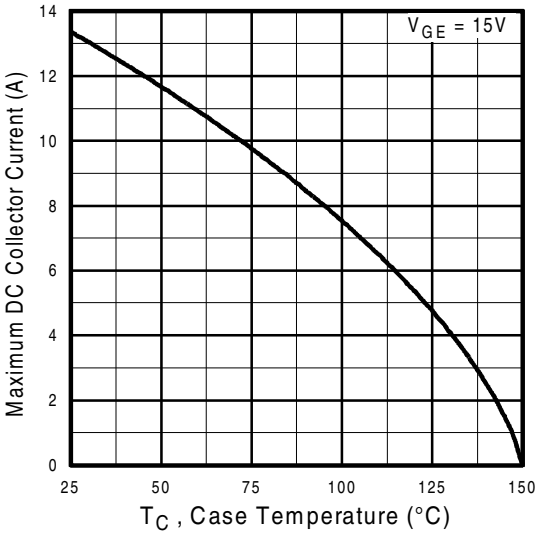



**Fig. 4** - Maximum Collector Current vs. Case Temperature

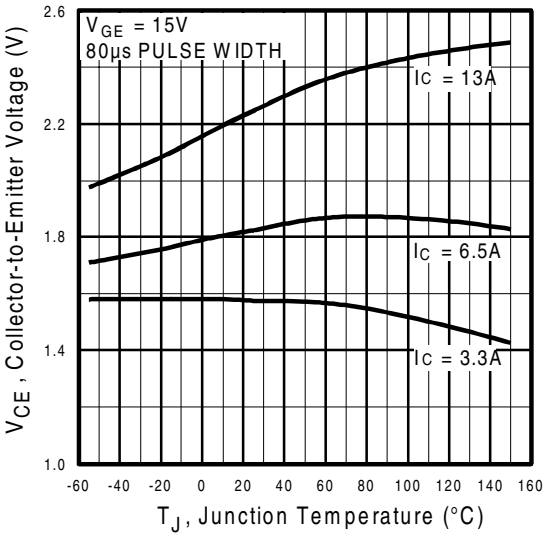



**Fig. 5** - Typical Collector-to-Emitter Voltage vs. Junction Temperature

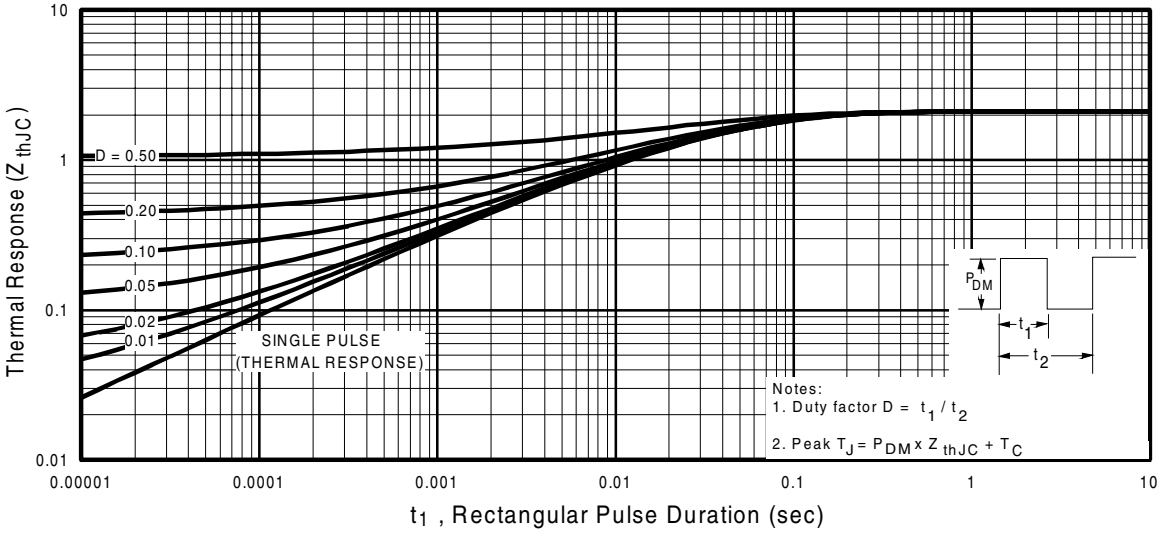



**Fig. 6** - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case

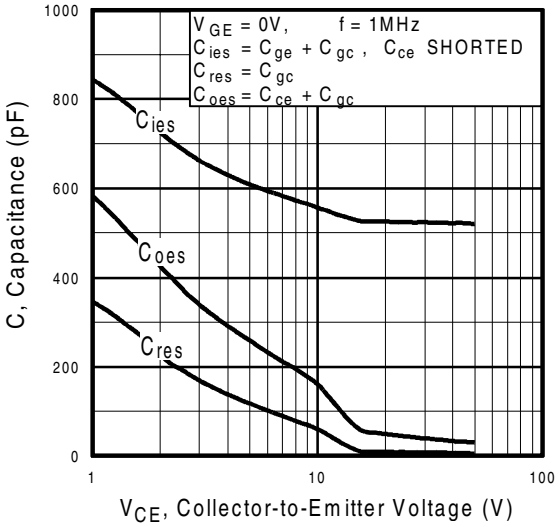



**Fig. 7 -** Typical Capacitance vs. Collector-to-Emitter Voltage

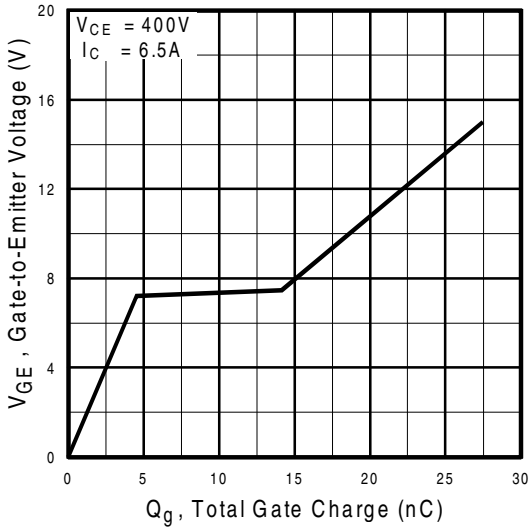



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage

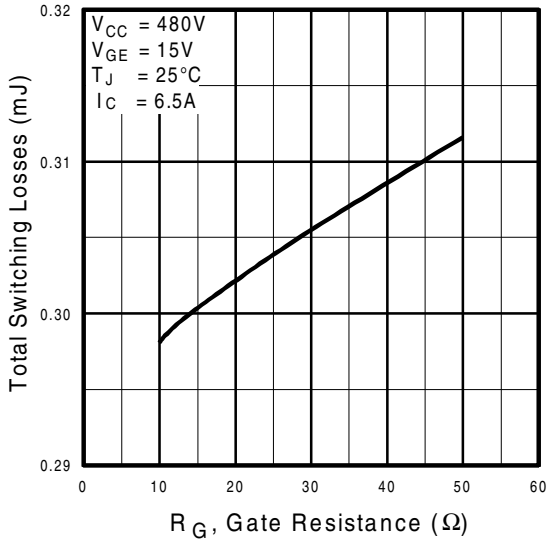



**Fig. 9** - Typical Switching Losses vs. Gate Resistance

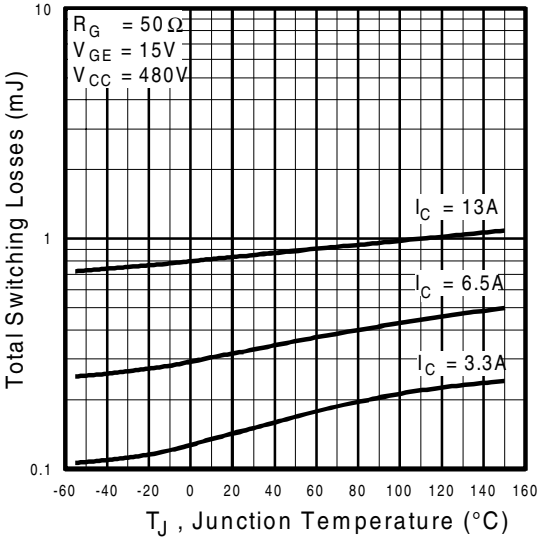



**Fig. 10** - Typical Switching Losses vs. Junction Temperature

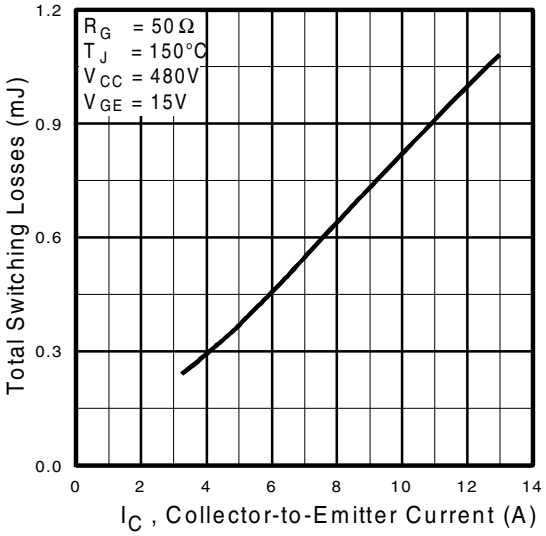



**Fig. 11 -** Typical Switching Losses vs. Collector-to-Emitter Current

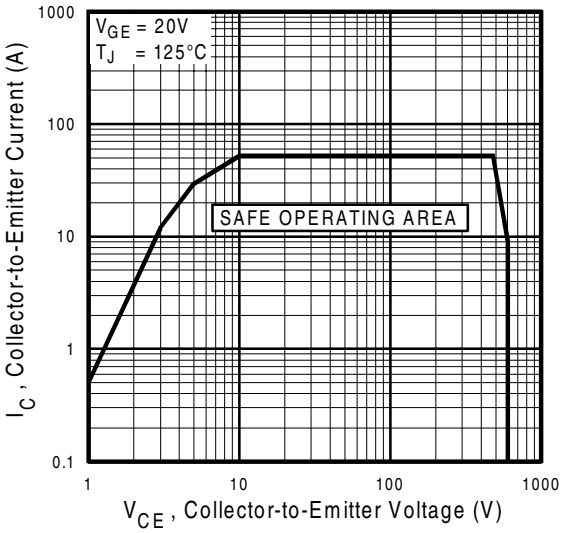



**Fig. 12** - Turn-Off SOA

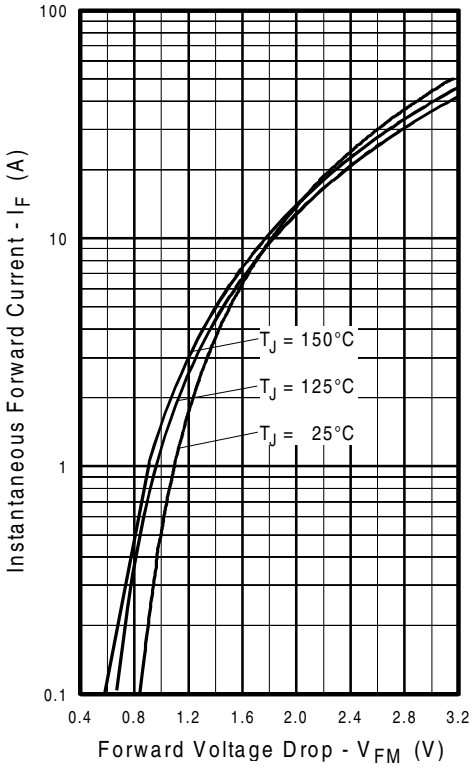



**Fig. 13** - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

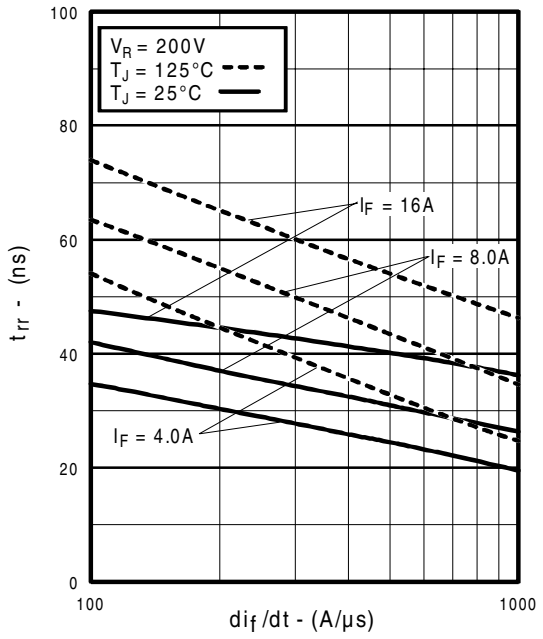



**Fig. 14** - Typical Reverse Recovery vs. $di_f/dt$

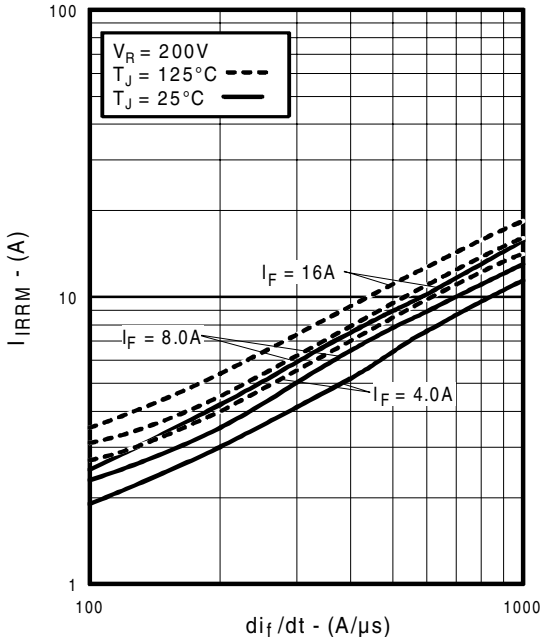



**Fig. 15** - Typical Recovery Current vs. $di_f/dt$

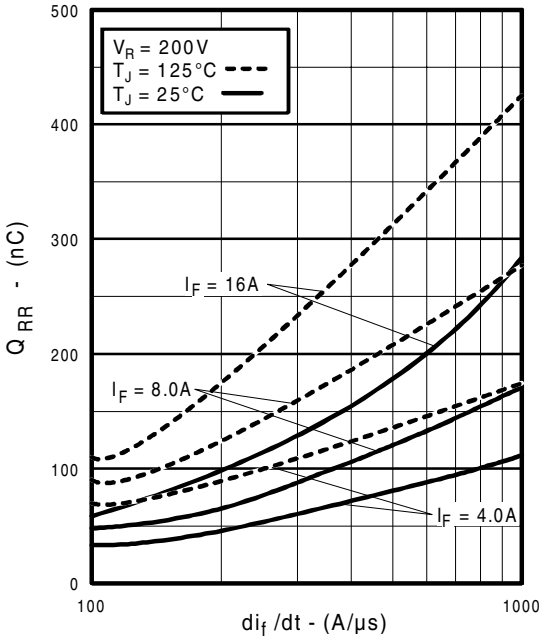



**Fig. 16** - Typical Stored Charge vs. $di_f/dt$

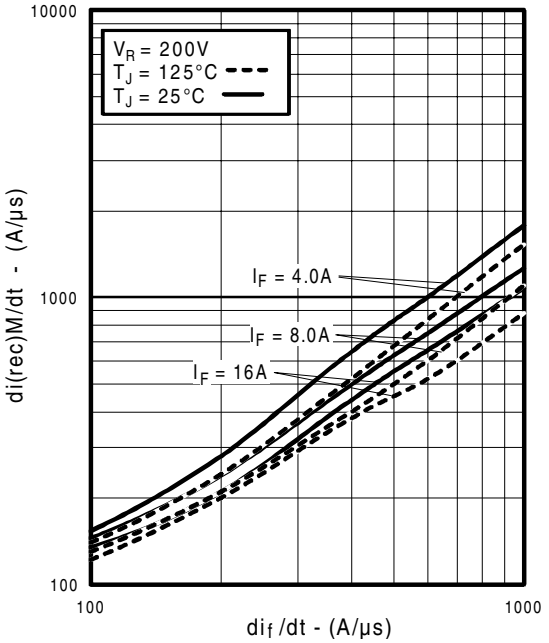



**Fig. 17** - Typical $di_{(rec)M}/dt$ vs. $di_f/dt$

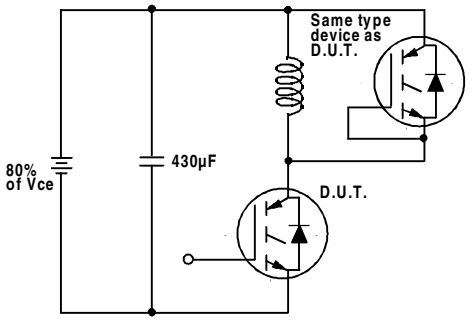



**Fig. 18a** - Test Circuit for Measurement of $I_{LM}$, $E_{on}$, $E_{off(diode)}$, $t_{rr}$, $Q_{rr}$, $I_{rr}$, $t_{d(on)}$, $t_r$, $t_{d(off)}$, $t_f$

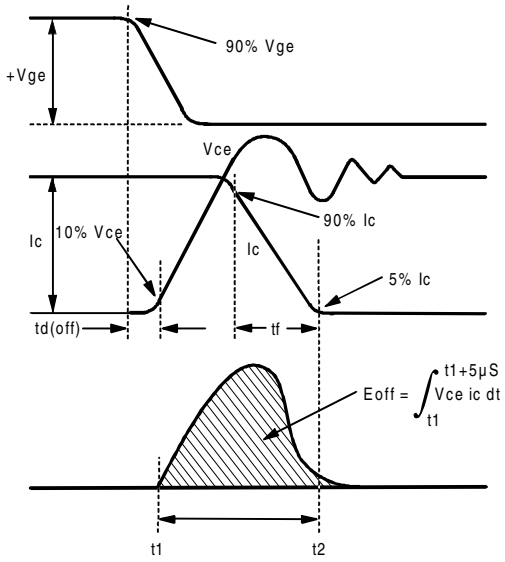



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining $E_{off}$, $t_{d(off)}$, $t_f$

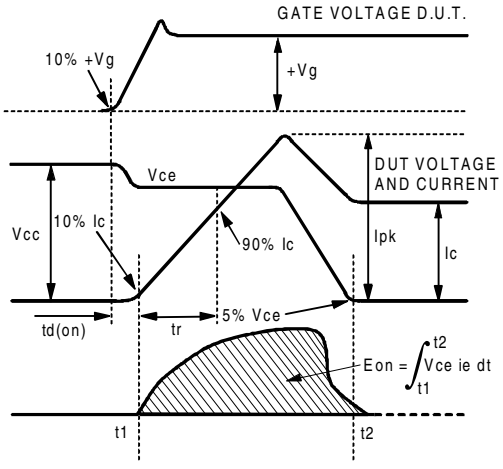



**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining $E_{on}$, $t_{d(on)}$, $t_r$

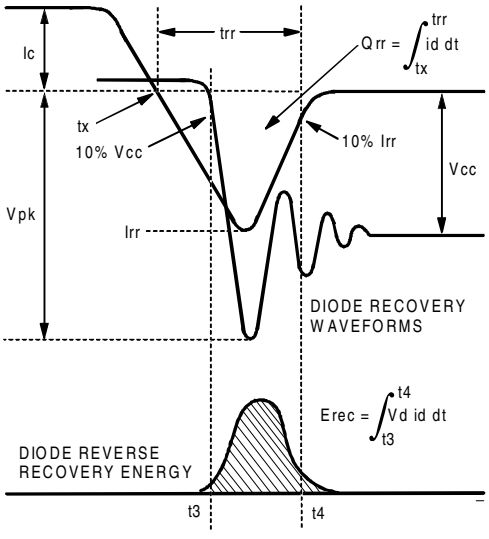



**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining $E_{rec}$, $t_{rr}$, $Q_{rr}$, $I_{rr}$

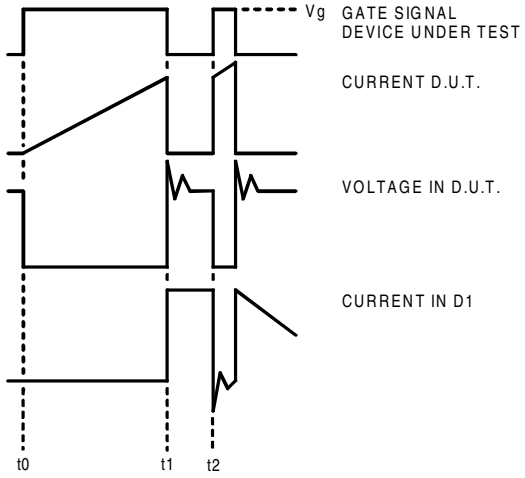



**Figure 18e.** Macro Waveforms for Figure 18a's Test Circuit

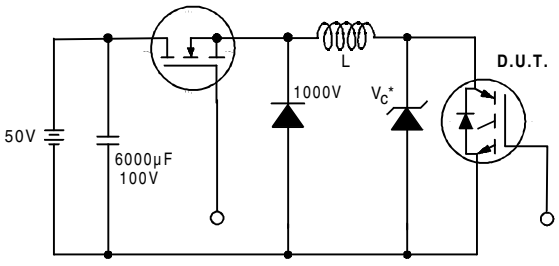



**Figure 19.** Clamped Inductive Load Test Circuit

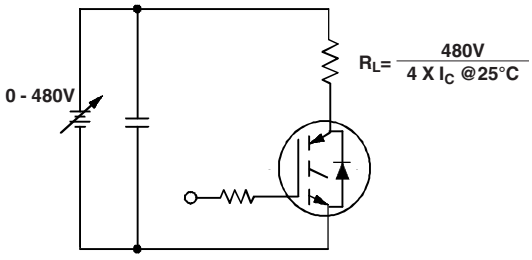



**Figure 20.** Pulsed Collector Current Test Circuit

## Notes:

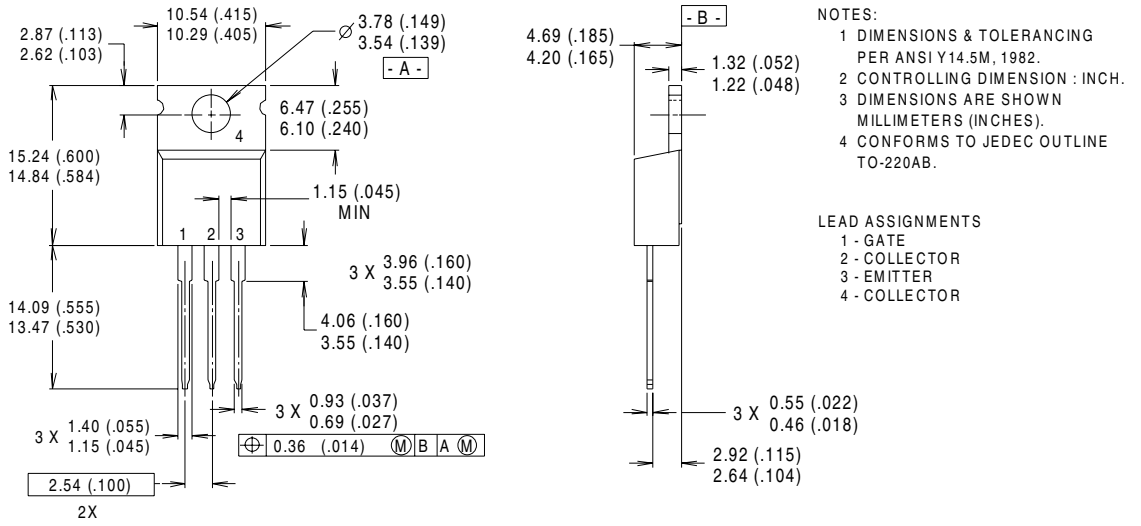
① Repetitive rating: $V_{GE}$=20V; pulse width limited by maximum junction temperature (figure 20)

② $V_{CC}$=80%($V_{CES}$), $V_{GE}$=20V, L=10µH, $R_G$ = 50Ω (figure 19)

③ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

④ Pulse width 5.0µs, single shot.

## Case Outline — TO-220AB




**CONFORMS TO JEDEC OUTLINE TO-220AB**
Dimensions in Millimeters and (Inches)

International
IOR Rectifier

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**IR CANADA:** 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200
**IR GERMANY:** Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 (0) 6172 96590
**IR ITALY:** Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 011 451 0111
**IR JAPAN:** K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171 Tel: 81 (0)3 3983 0086
**IR SOUTHEAST ASIA:** 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 (0)838 4630
**IR TAIWAN:**16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673 Tel: 886-(0)2 2377 9936
*Data and specifications subject to change without notice. 4/00*